Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in an ultra small DFN1110D-3 (SOT8015) leadless Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- Side wettable flanks for optical solder inspection
- Ultra small and leadless SMD plastic package: 1.1 x 1 x 0.48 mm
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (Class H1C)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-50	V	
V _{GS}	gate-source voltage			-20	-	12	V	
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-	-270	mA	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$		-	3.8	7.5	Ω	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D -
2	S	source		
3	D	drain	DFN1110D-3 (SOT8015)	G S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BSS84AKQB	DFN1110D-3	plastic, leadless extremely thin small outline package with side-wettable flanks (SWF); 3 terminals; 0.65 mm pitch; 1.1 mm x 1 mm x 0.48 mm body	SOT8015			

7. Marking

Table 4. Marking codes

Type number	Marking code
BSS84AKQB	В9

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-50	V
V _{GS}	gate-source voltage			-20	12	V
V _{GSMlim}	peak gate-source voltage	$\delta_{factor} = 0.1$; $t_p = 50 \mu s$		-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-270	mA
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-170	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-1.1	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	420	mW
			[1]	-	960	mW
		T _{sp} = 25 °C		-	4.2	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode			<u>'</u>		
Is	source current	T _{amb} = 25 °C	[1]	-	-115	mA
ESD maxim	um rating			1		
V _{ESD}	electrostatic discharge voltage	НВМ		-	1000	V
Avalanche r	uggedness			'		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.05 A; DUT in avalanche (unclamped)		-	1.2	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

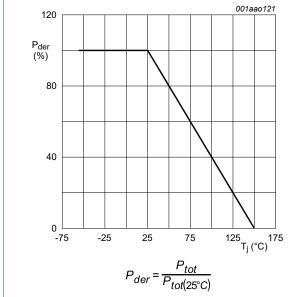


Fig. 1. Normalized total power dissipation as a function of junction temperature

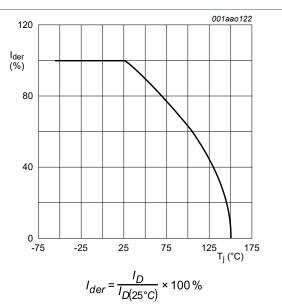


Fig. 2. Normalized continuous drain current as a function of junction temperature

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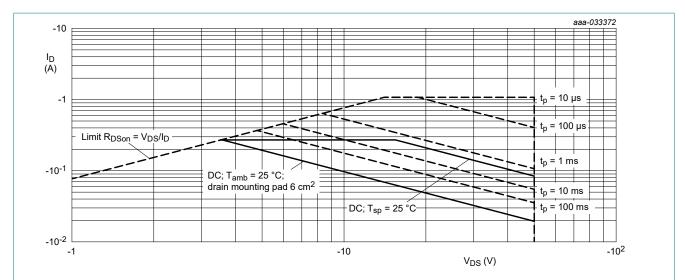


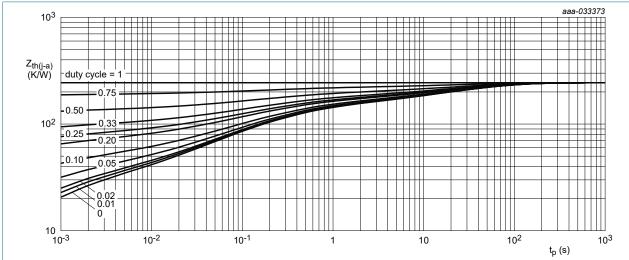
Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

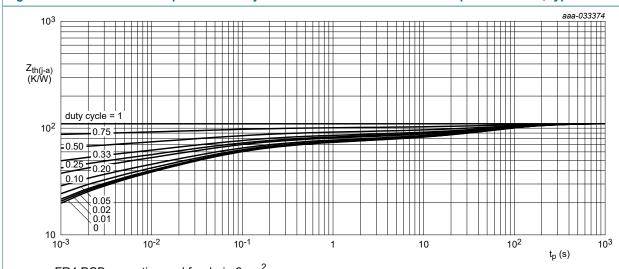
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	245	300	K/W
junction to	junction to ambient	to ambient	[2]	-	110	130	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-50	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	V _{DS} = -50 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	3.8	7.5	Ω
	resistance	V _{GS} = -10 V; I _D = -100 mA; T _j = 150 °C	-	6.7	13	Ω
		V_{GS} = -4.5 V; I_D = -100 mA; T_j = 25 °C	-	5	8.5	Ω
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	0.2	-	S
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -25 V; I_{D} = -0.1 A; V_{GS} = -10 V; T_{j} = 25 °C	-	0.4	0.6	nC
Q _{GS}	gate-source charge		-	0.1	-	nC
Q _{GD}	gate-drain charge	1	-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = -25 V; f = 1 MHz; V _{GS} = 0 V;	-	23.2	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	3.5	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -25 V; I _D = -0.1 A; V _{GS} = -10 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	9	-	ns
t _{d(off)}	turn-off delay time]	-	40	-	ns
t _f	fall time	1	-	22	-	ns
Source-drai	in diode		'			'
V _{SD}	source-drain voltage	I _S = -0.115 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.7	-1.2	V
t _{rr}	reverse recovery time	$I_S = -0.1 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	43	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = -25 V; T_j = 25 °C	-	39	-	nC

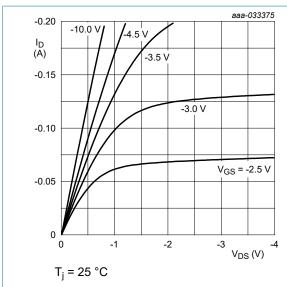


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

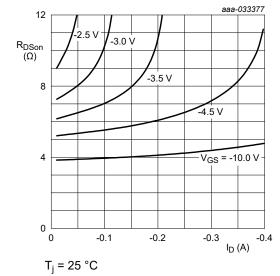
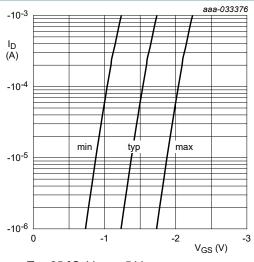


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

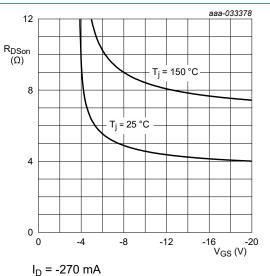


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

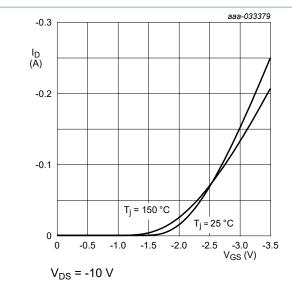


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

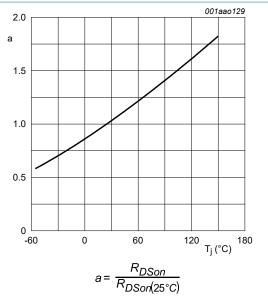


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

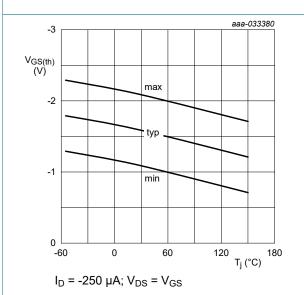
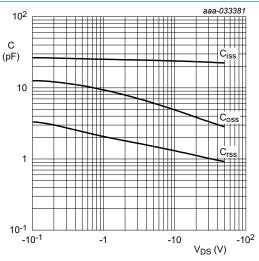


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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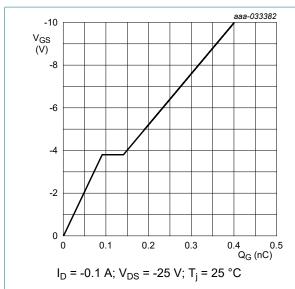


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

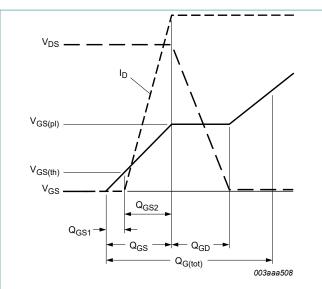


Fig. 15. Gate charge waveform definitions

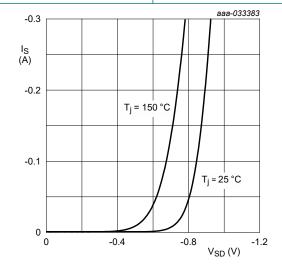
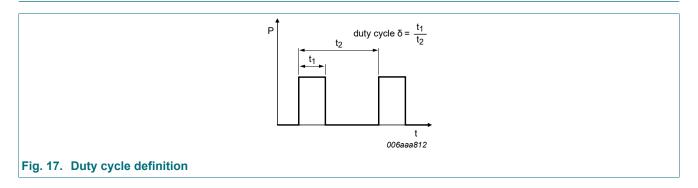


Fig. 16. Source current as a function of source-drain voltage; typical values

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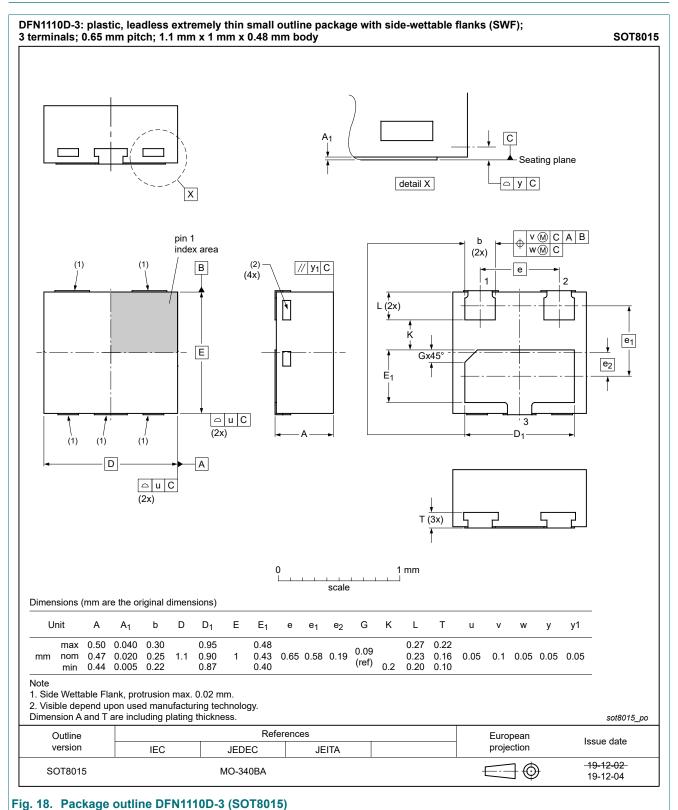
11. Test information



Quality information

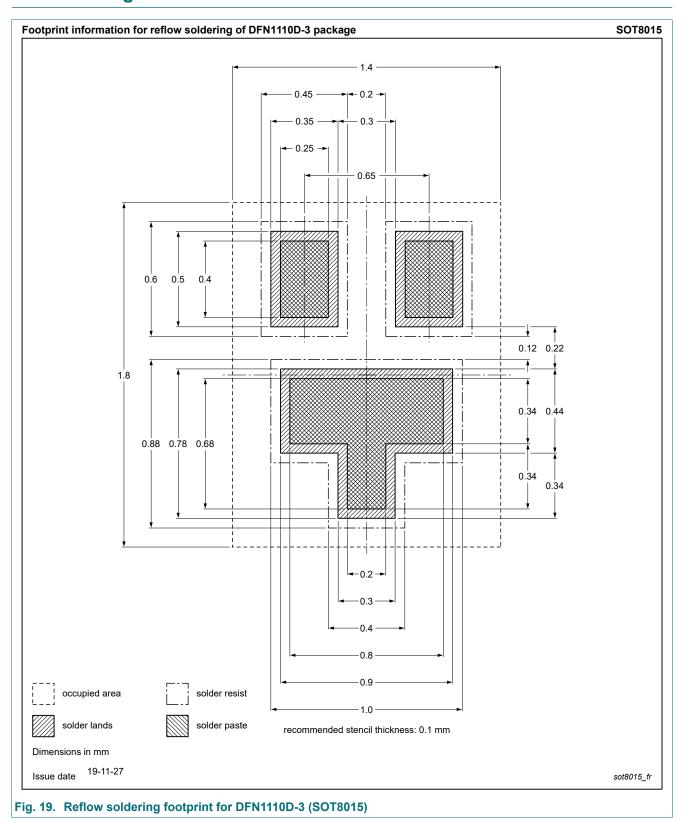
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



11 / 15

13. Soldering



50 V, P-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKQB v.1	20210713	Product data sheet	-	-

50 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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